

# **LMC835 Digital Controlled Graphic Equalizer**

## **General Description**

The LMC835 is a monolithic, digitally-controlled graphic equalizer CMOS LSI for Hi-Fi audio. The LMC835 consists of a Logic section and a Signal Path section made of analog switches and thin-film silicon-chromium resistor networks. The LMC835 is used with external resonator circuits to make a stereo equalizer with seven bands,  $\pm 12~{\rm dB}$  or  $\pm 6~{\rm dB}$  gain range and 25 steps each. Only three digital inputs are needed to control the equalization. The LMC835 makes it easy to build a  $\mu P\text{-}{\rm controlled}$  equalizer.

The signal path is designed for very low noise and distortion, resulting in very high performance, compatible with PCM audio.

#### **Features**

- No volume controls required
- Three-wire interface
- 14 bands, 25 steps each
- $\blacksquare$   $\pm$ 12 dB or  $\pm$ 6 dB gain ranges
- Low noise and distortion
- TTL, CMOS logic compatible

## **Applications**

- Hi-Fi equalizer
- Receiver■ Car stereo
- Cai steleo
- Musical instrument
- Tape equalization
- Mixer
- Volume controller

A<sub>IN6</sub>

A<sub>IN5</sub>

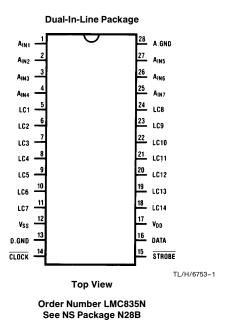
A. GND

A<sub>IN 1</sub>

 $A_{IN2}$ 

A<sub>IN3</sub>

# **Connection Diagrams**



Top View

Order Number LMC835V
See NS Package V28A

**Molded Chip Carrier Package** 

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LC14

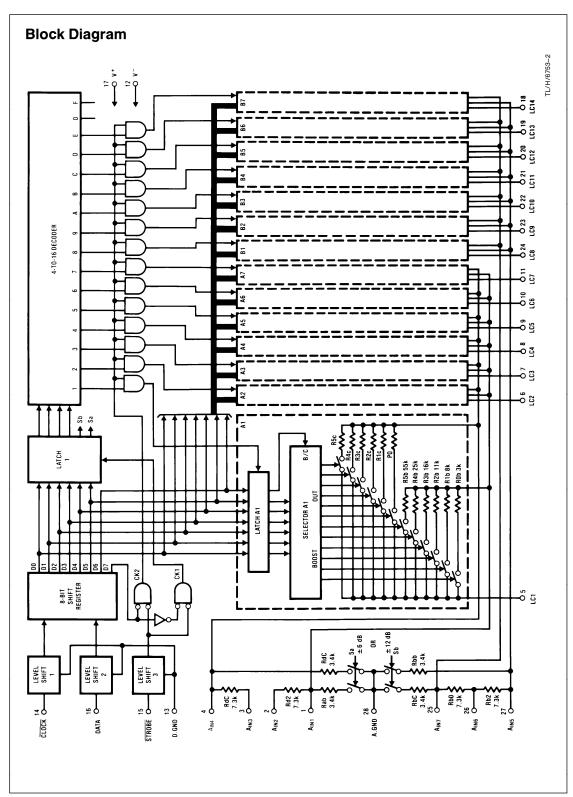
 $V_{DD}$ 

DATA
STROBE

CLOCK

D. GND

TL/H/6753-26



## **Absolute Maximum Ratings**

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage,  $V_{DD}-V_{SS}$  18V Allowable Input Voltage (Note 1)  $V_{SS}-0.3V$ 

 $\label{eq:toVDD} \begin{array}{c} \text{to V}_{DD} + 0.3 \text{V} \\ \text{Storage Temperature, T}_{\text{stg}} & -60^{\circ}\text{C to} + 150^{\circ}\text{C} \\ \end{array}$ 

 $\label{eq:lead-temperature} \textit{Lead Temperature (Soldering, 10 sec), N Pkg} \\ \phantom{\text{Lead Temperature (Soldering, 10 sec), N Pkg}} + 260^{\circ} \text{C}$ 

Lead Temperature, V Pkg

 Vapor Phase (60 sec)
 + 215°C

 Infrared (15 sec)
 + 220°C

# **Operating Ratings**

 $\begin{array}{lll} \mbox{Supply Voltage, V}_{\mbox{DD}} - \mbox{V}_{\mbox{SS}} & \mbox{5V to 16V} \\ \mbox{Digital Ground (Pin 13)} & \mbox{V}_{\mbox{SS}} \mbox{ to V}_{\mbox{DD}} \\ \mbox{Digital Input (Pins 14, 15, 16)} & \mbox{V}_{\mbox{SS}} \mbox{ to V}_{\mbox{DD}} \end{array}$ 

Analog Input (Pins 1, 2, 3, 4, 25, 26, 27)

(Note 1)  $V_{SS}$  to  $V_{DD}$  Operating Temperature,  $T_{opr}$   $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$ 

# **Electrical Characteristics** (Note 2) $V_{DD} = 7.5V$ , $V_{SS} = -7.5V$ , A.GND = 0V LOGIC SECTION

Symbol	Parameter	Test Conditions	Тур	Tested Limit (Note 3)	Design Limit (Note 4)	Unit (Limit)
I <sub>DDL</sub>	Supply Current	Pins 14, 15, 16 are 0V	0.01	0.5	0.5	mA (Max)
I <sub>SSL</sub>		Pins 14, 15, 16 are 0V	0.01	0.5	0.5	mA (Max)
I <sub>DDH</sub>		Pins 14, 15, 16 are 5V	1.3	5	5	mA (Max)
I <sub>SSH</sub>		Pins 14, 15, 16 are 5V	0.9	5	5	mA (Max)
$V_{IH}$	High-Level Input Voltage	@Pins 14, 15, 16	1.8	2.3	2.5	V (Min)
V <sub>IL</sub>	Low-Level Input Voltage	@Pins 14, 15, 16	0.9	0.6	0.4	V (Max)
f <sub>o</sub>	Clock Frequency	@Pin 14	2000	500	500	kHz (Max)
tw(STB)	Width of STB Input	See Figure 1	0.25	1	1	μs (Min)
t <sub>setup</sub>	Data Setup Time	See Figure 1	0.25	1	1	μs (Min)
t <sub>hold</sub>	Data Hold Time	See Figure 1	0.25	1	1	μs (Min)
t <sub>cs</sub>	Delay from Rising Edge of $\overline{\text{CLOCK}}$ to $\overline{\text{STB}}$	See Figure 1	0.25	1	1	μs (Min)
I <sub>IN</sub>	Input Current	@Pins 14, 15, 16 0V < V <sub>IN</sub> < 5V	±0.01	±1		μΑ (Max)
C <sub>IN</sub>	Input Capacitance	@Pins 14, 15, 16 f = 1 MHz	5			pF

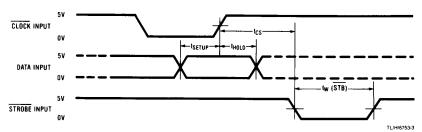
Note 1: Pins 2, 3 and 26 have a maximum input voltage range of  $\pm$ 22V for the typical application shown in Figure 7.

Note 2: Bold numbers apply at temperature extremes. All other numbers apply at T<sub>A</sub> = 25°C, V<sub>DD</sub> = 7.5V, V<sub>SS</sub> = -7.5V, D.GND = A.GND = 0V as shown in the test circuit, Figures 3 and 4.

Note 3: Guaranteed and 100% production tested.

Note 4: Guaranteed (but not 100% production tested) over the operating temperature range. These limits are not used to calculate outgoing quality levels.

# **Timing Diagram**



TL/H/6753-3

Note: To change the gain of the presently selected band, it is not necessary to send DATA 1 (Band Selection) each time.

FIGURE 1

# **Electrical Characteristics** (Note 2) $V_{DD} = 7.5V$ , $V_{SS} = -7.5V$ , D.GND = A.GND = 0V

#### SIGNAL PATH SECTION

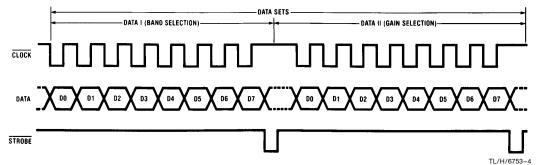
Symbol	Parameter	Test Conditions	Тур	Tested Limit (Note 3)	Design Limit (Note 4)	Unit (Limit)
EA	Gain Error	A <sub>V</sub> =0 dB @ ± 12 dB Range	0.1	0.5	0.5	dB (Max)
**		A <sub>V</sub> =0 dB @ ± 6 dB Range	0.1	1	1	dB (Max)
		$A_V = \pm 1 \text{ dB } @ \pm \text{ dB Range}$	0.1	0.5	0.6	dB (Max)
		(R <sub>5b</sub> or R <sub>5c</sub> is ON)				
		$A_V$ = ±2 dB @ ± 12 dB Range	0.1	0.5	0.6	dB (Max)
		(R <sub>4b</sub> or R <sub>4c</sub> is ON)				
		$A_V = \pm 3 \text{ dB } @ \pm 12 \text{ dB Range}$	0.1	0.5	0.6	dB (Max)
		(R <sub>3b</sub> or R <sub>3c</sub> is ON)				
		$A_V$ = ±4 dB @ ± 12 dB Range	0.1	0.5	0.7	dB (Max)
		(R <sub>2b</sub> or R <sub>2c</sub> is ON)		0.5		ID (14 )
		A <sub>V</sub> = ±5 dB @ ± 12 dB Range	0.1	0.5	0.7	dB (Max)
		(R <sub>1b</sub> or R <sub>1c</sub> is ON)	0.0	1	4.0	dD (May)
		$A_V = \pm 9 \text{ dB } @ \pm 12 \text{ dB Range}$	0.2	'	1.3	dB (Max)
		(R <sub>0b</sub> or R <sub>0c</sub> is ON)				
THD	Total Harmonic	$A_V = 0 \text{ dB } @ \pm 12 \text{ dB Range}$	0.0015			%
	Distortion	$V_{IN} = 4V_{rms}$ , $f = 1 \text{ kHz}$				
		A <sub>V</sub> = 12 dB @ ± 12 dB Range				
		$V_{IN} = 1V_{rms}$ , $f = 1 \text{ kHz}$	0.01	0.1		% (Max)
		$V_{IN} = 1V_{rms}, f = 20 \text{ kHz}$	0.1	0.5		% (Max)
		$A_V = -12 \text{ dB } @ \pm 12 \text{ dB Range}$	0.04			0/ (14)
		$V_{IN} = 4V_{rms}, f = 1 \text{ kHz}$	0.01 0.1	0.1 0.5		% (Max) % (Max)
		$V_{IN} = 4V_{rms}$ , f = 20 kHz				` ′
V <sub>O Max</sub>	Maximum Output Voltage	A <sub>V</sub> =0 dB @ ±12 dB Range	5.5	5.1	5	V <sub>rms</sub> (Min)
		THD < 1%, f = 1 kHz				
S/N	Signal to Noise Ratio	$A_V = 0$ dB @ $\pm$ 12 dB Range	114			dB
		V <sub>ref</sub> =1 V <sub>rms</sub>				
		$A_V$ = 12 dB @ $\pm$ 12 dB Range	106			dB
		$V_{ref} = 1V_{rms}$				
		$A_V = -12 \text{ dB } @ \pm 12 \text{ dB Range}$	116			dB
		$V_{ref} = 1V_{rms}$				
I <sub>LEAK</sub>	Leakage Current	$A_V = 0$ dB @ $\pm$ 12 dB Range				
	_	(All internal switches are OFF)				
		Pin 2+3, Pin 26		500		nA (Max)
		Pin 5 ~ Pin 11, Pin 18 ~ Pin 24		50		nA (Max)

Note 2; Boldface numbers apply at temperature extremes. All other numbers apply at T<sub>A</sub>=25°C, V<sub>DD</sub>=7.5V, V<sub>SS</sub>=-7.5V, D.GND=A.GND=0V as shown in the test circuit, Figures 3 and 4.

Note 3: Guaranteed and 100% production tested.

Note 4: Guaranteed (but not 100% production tested) over the operating temperature range. These limits are not used to calculate outgoing quality levels.

# **Timing Diagrams**



Note: To change the gain of the presently selected band, it is not necessary to send DATA 1 (Band Selection) each time.

FIGURE 2

#### **Truth Tables**

DATA I (Band Selection)

D7	D6	D5	D4	D3	D2	D1	D0
Н	Х	L	L	L	L	L	L
Н	Х	L	L	L	L	L	Н
Н	Х	L	L	L	L	Н	L
Н	Х	L	L	L	L	Н	Н
Н	Х	L	L	L	Н	L	L
H	Х	L	L	L	Н	L	Н
Н	Х	L	L	L	Н	Н	L
Н	Х	L	L	L	Н	Н	Н
Н	Х	L	L	Н	L	L	L
Н	Х	L	L	Н	L	L	Н
Н	Х	L	L	Н	L	Н	L
Н	Х	L	L	Н	L	Н	Н
Н	Х	L	L	Н	Н	L	L
Н	Х	L	L	Н	Н	L	Н
Н	Х	L	L	Н	Н	Н	L
Н	Х	L	L	Н	Н	Н	Н
Н	Х	L	Н	V	alid Bin	ary Inp	ut
Н	Х	Н	L	V	alid Bin	ary Inp	ut
Н	Х	Н	Н	V	alid Bin	ary Inp	ut
1	1	1	1	←	Band	Code	$\rightarrow$
①	2	3	4				

(Ch A: Band 1  $\sim$  7, Ch B: Band 8  $\sim$  14)

Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, No Band Selection Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, Band 1

Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, Band 2

Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, Band 3

Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, Band 4

Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, Band 5

Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, Band 6

Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, Band 7

Ch A  $\pm\,$  12 dB Range, Ch B  $\pm\,$  12 dB Range, Band 8

Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, Band 9 Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, Band 10

Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, Band 10 Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, Band 11

Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, Band 11 Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, Band 12

Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, Band 13

Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, Band 14

Ch A  $\pm$  12 dB Range, Ch B  $\pm$  12 dB Range, No Band Selection

Ch A  $\pm$  12 dB Range, Ch B  $\pm$  6 dB Range, Band 1  $\sim$  14

Ch A  $\pm$  6 dB Range, Ch B  $\pm$  12 dB Range, Band 1  $\sim$  14

Ch A  $\pm$  6 dB Range, Ch B  $\pm$  6 dB Range, Band 1  $\sim$  14

- ① DATA 1
- @ Don't Care
- 4 Ch B  $\pm 6$  dB/ $\pm 12$  dB Range

# DATA II (Gain Selection)

BATA II (Gain colection)							
D7	D6	D5	D4	<b>D</b> 3	D2	D1	D0
L	Х	L	L	L	L	L	L
L	Н	Н	L	L	L	L	L
L	Н	L	Н	L	L	L	L
L	Н	L	L	Н	L	L	L
L	Н	L	L	L	Н	L	L
L	Н	L	L	L	L	Н	L
L	Н	L	Н	L	L	Н	L
L	Н	Н	L	Н	L	Н	L
L	Н	L	Н	L	Н	Н	L
L	Н	L	L	L	L	L	Н
L	Н	Н	L	Н	L	L	Н
L	Н	Н	L	Н	Н	L	Н
L	Н	Н	L	Н	Н	Н	Н
L	L		Valid Above Input				
1	1		←	Gain	Code	$\rightarrow$	
<b>6</b>	ക						

- This is the gain if the  $\pm 12$  dB range is selected by DATA I. If the  $\pm 6$  dB range is selected, then the values shown must be approximately halved. See the characteristics curves for more exact data.
- © DATA II

Flat

1 dB Boost 2 dB Boost 3 dB Boost 4 dB Boost 5 dB Boost

6 dB Boost

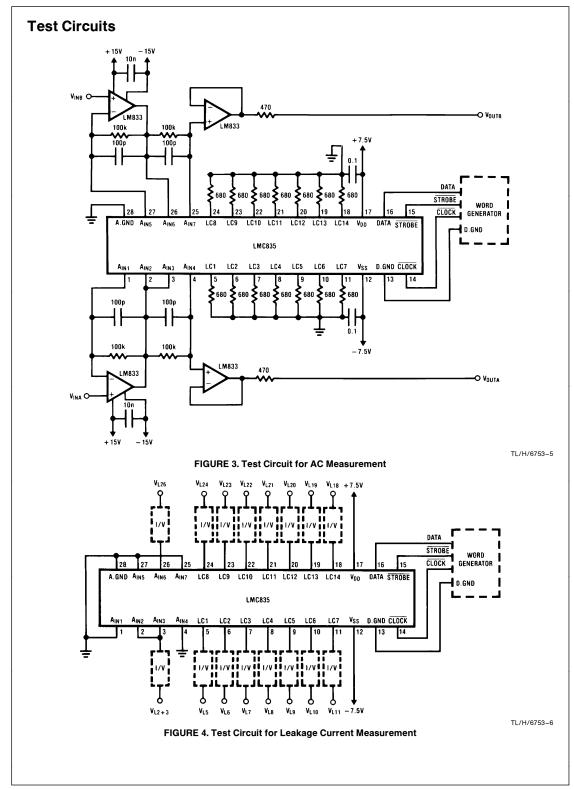
7 dB Boost

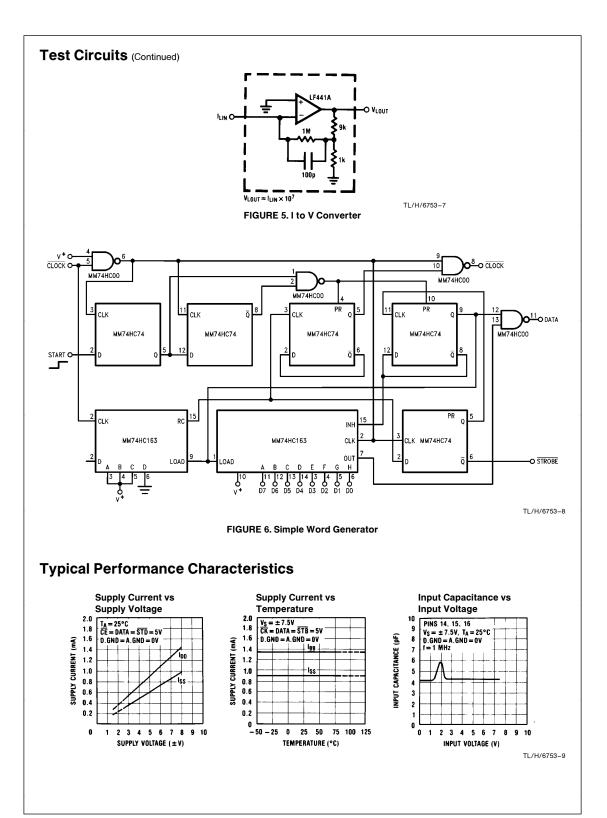
8 dB Boost

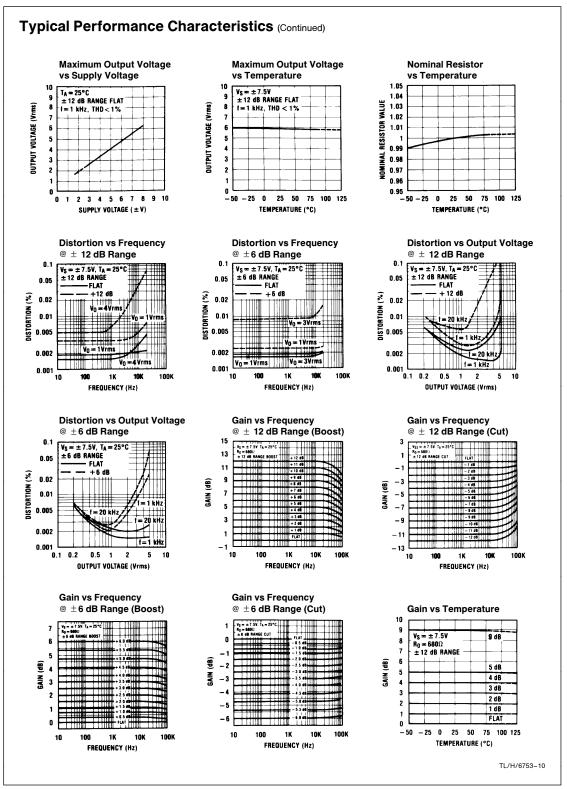
9 dB Boost

10 dB Boost 11 dB Boost 12 dB Boost 1 dB ~ 12 dB Cut

Boost/Cut





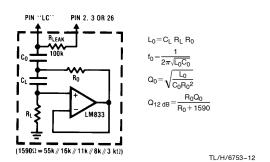


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FIGURE 7. Stereo 7-Band Equalizer

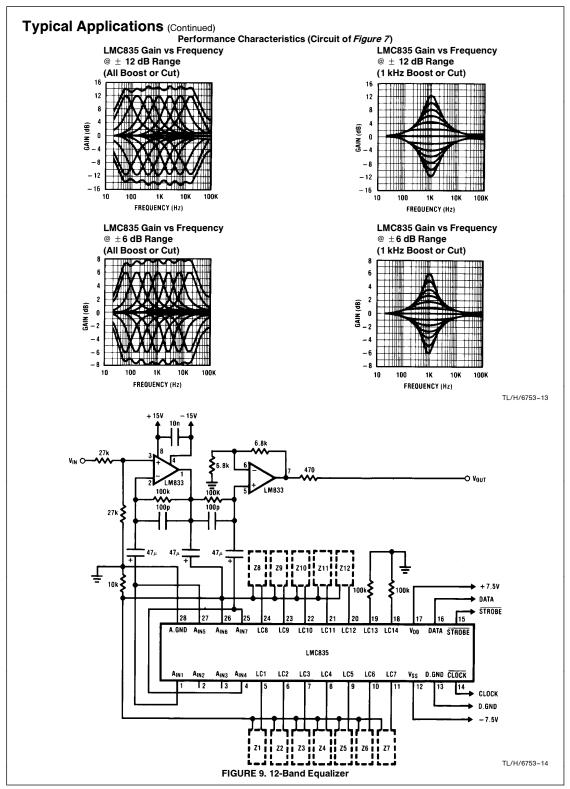
**TABLE I: Tuned Circuit Elements** 

	Q <sub>0</sub> =3.5, Q <sub>12dB</sub> =1.05							
<b>Z</b> 1	f <sub>o</sub> (Hz)	C <sub>O</sub> (F)	C <sub>L</sub> (F)	$R_L(\Omega)$	$R_{O}(\Omega)$			
Z1	63	1μ	0.1μ	100k	680			
Z2	160	$0.47\mu$	0.033μ	100k	680			
Z3	400	$0.15\mu$	0.015μ	100k	680			
Z4	1k	$0.068\mu$	$0.0068 \mu$	82k	680			
Z5	2.5k	$0.022 \mu$	$0.0033 \mu$	82k	680			
Z6	6.3k	$0.01\mu$	0.0015μ	62k	680			
Z7	16k	$0.0047\mu$	680p	47k	680			



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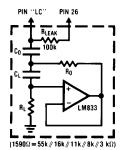
FIGURE 8. Tuned Circuit for Stereo 7-Band Equalizer (Figure 7)



# Typical Applications (Continued)

**TABLE II. Tuned Circuit Elements** 

Q <sub>0</sub> = 4.7, Q <sub>12 dB</sub> = 1.4							
	f <sub>o</sub> (Hz)	C <sub>o</sub> (F)	C <sub>L</sub> (F)	$R_L(\Omega)$	$R_o(\Omega)$		
Z1	16	3.3µ	0.47μ	100k	680		
Z2	31.5	15μ	0.22μ	110k	680		
Z3	63	1μ	0.1μ	100k	680		
Z4	125	$0.39\mu$	0.068μ	91k	680		
Z5	250	0.22μ	0.033μ	82k	680		
Z6	500	0.1μ	0.015μ	100k	680		
Z7	1k	0.047μ	0.01μ	82k	680		
Z8	2k	0.022μ	0.0047μ	91k	680		
Z9	4k	0.01μ	0.0022μ	110k	680		
Z10	8k	$0.0068 \mu$	0.001μ	82k	680		
Z11	16k	$0.0033 \mu$	680p	62k	680		
Z12	32k	$0.0015\mu$	470p	68k	510		



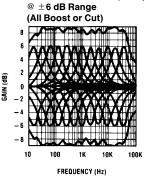


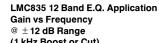
TL/H/6753-15

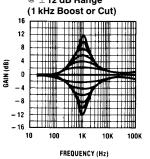
FIGURE 10. Tuned Circuit for 12-Band Equalizer (Figure 9)

#### Performance Characteristics (Circuit of Figure 9)

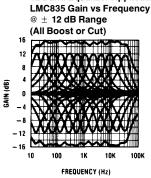
12 Band Equalizer Application LMC835 Gain vs Frequency



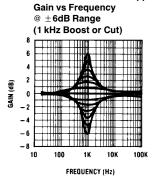




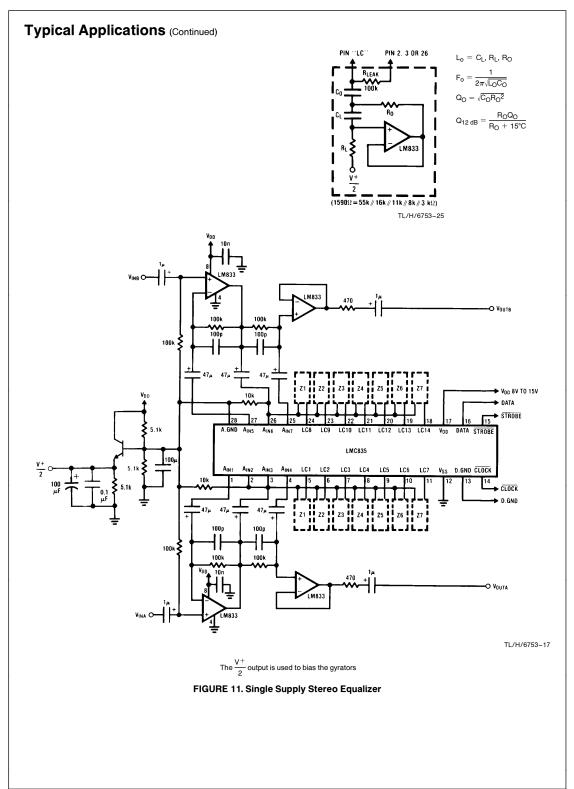
# 12 Band Equalizer Application

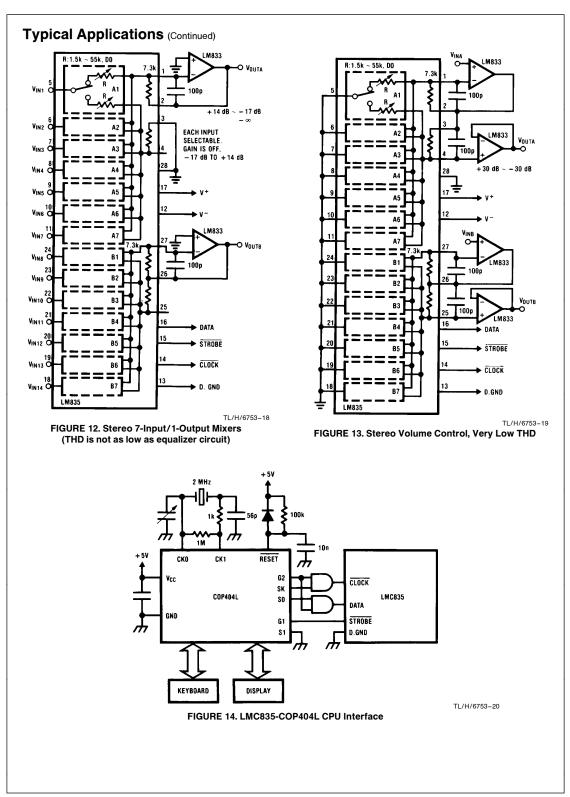


# LMC835 12 Band E.Q. Application



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# Typical Applications (Continued)

#### Sample Subroutine Program for Figure 14, LMC835-COP404L CPU Interface

CODE         LABEL         MNEMONICS         COMMENTS           3F         LMC835:         LBI         3F         ;POINT TO RAMADDRESS 3F           05         SEND         LD         ;RAMDATA TO A           22         SC         ; SET CARRY           335F         OGI         ;SET PORT G= 1111, OPEN THE AND GATES           4F         XAS         ;SWAP A AND SIO, CLOCK START           05         LD         ;RAMDATA TO A, MAKE SURE A = DATA           07         XDS         ;SWAP A AND RAMDATA, RAMADDRESS=RAMADD           05         LD         ;RAMDATA TO A           4F         XAS         ;SWAP A AND SIO           05         LD         ;RAMDATA TO A, MAKE SURE A=NEWDATA           07         XDS         ;SWAP A AND RAMDATA, RAMADDRESS=RAMADD	
05         SEND         LD         ;RAMDATA TO A           22         SC         ;SET CARRY           335F         OGI         ;SET PORT G= 1111, OPEN THE AND GATES           4F         XAS         ;SWAP A AND SIO, CLOCK START           05         LD         ;RAMDATA TO A, MAKE SURE A = DATA           07         XDS         ;SWAP A AND RAMDATA, RAMADDRESS=RAMADD           05         LD         ;RAMDATA TO A           4F         XAS         ;SWAP A AND SIO           05         LD         ;RAMDATA TO A, MAKE SURE A=NEWDATA	
22       SC       ; SET CARRY         335F       OGI       ; SET PORT G= 1111, OPEN THE AND GATES         4F       XAS       ; SWAP A AND SIO, CLOCK START         05       LD       ; RAMDATA TO A, MAKE SURE A = DATA         07       XDS       ; SWAP A AND RAMDATA, RAMADDRESS=RAMADD         05       LD       ; RAMDATA TO A         4F       XAS       ; SWAP A AND SIO         05       LD       ; RAMDATA TO A, MAKE SURE A=NEWDATA	
335F         OGI         ;SET PORT G= 1111, OPEN THE AND GATES           4F         XAS         ;SWAP A AND SIO, CLOCK START           05         LD         ;RAMDATA TO A, MAKE SURE A = DATA           07         XDS         ;SWAP A AND RAMDATA, RAMADDRESS=RAMADD           05         LD         ;RAMDATA TO A           4F         XAS         ;SWAP A AND SIO           05         LD         ;RAMDATA TO A, MAKE SURE A=NEWDATA	
4F XAS ;SWAP A AND SIO, CLOCK START  05 LD ;RAMDATA TO A, MAKE SURE A = DATA  07 XDS ;SWAP A AND RAMDATA, RAMADDRESS=RAMADD  05 LD ;RAMDATA TO A  4F XAS ;SWAP A AND SIO  05 LD ;RAMDATA TO A, MAKE SURE A=NEWDATA	
05       LD       ;RAMDATA TO A, MAKE SURE A = DATA         07       XDS       ;SWAP A AND RAMDATA, RAMADDRESS=RAMADD         05       LD       ;RAMDATA TO A         4F       XAS       ;SWAP A AND SIO         05       LD       ;RAMDATA TO A, MAKE SURE A=NEWDATA	
7 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3	
05 LD ;RAMDATA TO A 4F XAS ;SWAP A AND SIO 05 LD ;RAMDATA TO A, MAKE SURE A=NEWDATA	
4F XAS ;SWAP A AND SIO 05 LD ;RAMDATA TO A, MAKE SURE A=NEWDATA	RESS-1
05 LD ;RAMDATA TO A, MAKE SURE A=NEWDATA	
,	
07 XDS ;SWAP A AND RAMDATA, RAMADDRESS=RAMADD.	
	RESS-1
32 RC ;RESET CARRY	
4F XAS ;SWAP A AND SIO, CLOCK STOP	
335D OGJ 13 ;SET PORT G=1101, MAKE STROBE LOW	
335B OGI 11 ;SET PORT G=1011, MAKE STROBE HIGH, CLO	SE THE
GATES	
4E CBA ;BD TO A	
43 AISC 3 ;RAMADDRESS < 3C THEN RETURN	
48 RET	
80 JP SEND	
RAM	
ADDRESS COMMENTS	
3C DATA ;GAIN DATA D4-D7	
3D DATA ;GAIN DATA DO-D3	
3E DATA ;BAND DATA D4-D7	
3F DATA ;BAND DATA DO-D3	

## **Application Hints**

#### **SWITCHING NOISE**

The LMC835 uses CMOS analog switches that have small leakages (less than 50 nA). When a band is selected for flat gain, all the switches in that band are open and the resonator circuit is not connected to the LMC835 resistor network. It is only in the flat mode that the small leakage currents can cause problems. The input to the resonator circuit is usually a capacitor and the leakage currents will slowly charge up this capacitor to a large voltage if there is no resistive path to limit it. When the band is set to any value other than flat, the charge on the capacitor will be discharged by the resistor network and there will be a transient at the output. To limit the size of this transient, R<sub>LEAK</sub> is necessary.

# HOW TO AVOID SWITCHING NOISE DUE TO LEAKAGE CURRENT (Refer to Figures 7 and 8)

To avoid switching noise due to leakage currents when changing the gain, it is recommended to put  $R_{LEAK}=100~\rm k\Omega$  between Pin 3 and Pin 5—11 each, Pin 26 and Pin 12—24 each. The resistor limits the voltage that the capacitor can charge to, with minimal effects on the equalization. The frequency response change due to  $R_{LEAK}$  are shown in Figure 15. The gain error is only 0.2 dB and Q error is only 5% at 12 dB boost or cut.

#### **SIMPLE WORD GENERATOR** (Figure 6)

Circuit operation revolves around an MM74HC165 parallel-in/serial-out shift register. Data bits D0 through D7 are applied to the parallel of the MM74HC165 from 8 toggle switches. The bits are shifted out to the DATA input of the LMC835 in sync with the clock. When all data bits have been loaded, CLOCK is inhibited and a STROBE pulse is generated: this sequence is initiated by a START pulse.

#### LMC835-COP404L CPU INTERFACE (Refer to Figure 14)

The diagram shows AND gates between the COP and the LMC835. These permit G2 to inhibit the CLOCK and DATA lines (SK and SO) during a STROBE (G1) pulse. This function may also be implemented in software. As shown in *Figure 2*, the data groups are shifted in D0 first. Data is loaded on positive clock edges.

#### POWER SUPPLIES

These applications show LM317/337 regulators for the  $\pm 7.5 \text{V}$  supplies for the LMC835. Since the latter draws only 5 mA max., 1k series dropping resistors from the  $\pm 15 \text{V}$  op amp supply and a pair of 7.5 V zeners and bypass caps will also suffice.

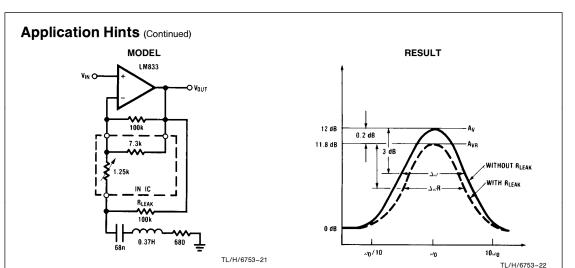


FIGURE 15. Effect of R<sub>LEAK</sub>

#### REDUCING EXTERNAL COMPONENTS

The typical application shown in Figure 7 is switching noise free. The DC-coupled circuit in Figure 16 is also switching noise free, except at 12 dB/6 dB switch turn ON/OFF. This switching noise is caused by the  $\rm I_{bias}$  and  $\rm V_{offset}$  of the op

amps. Selecting a low  $l_{bias}$  and  $V_{offset}$  op amp can minimize the switching noise due to the 12 dB/6 dB switch. The DC-coupled application can also eliminate the  $R_F=100k$  resistors with only a 0.5 dB gain error at 12 dB boost or cut.

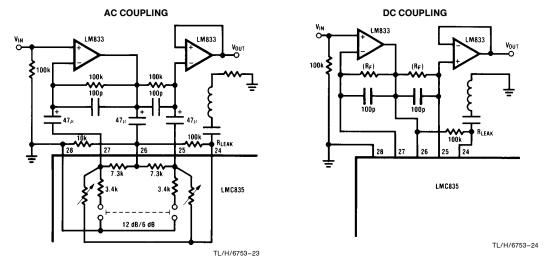
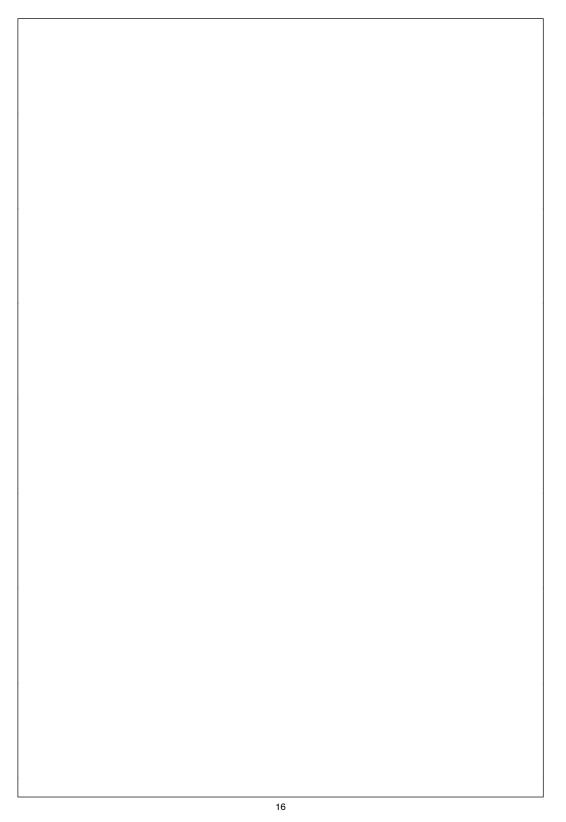
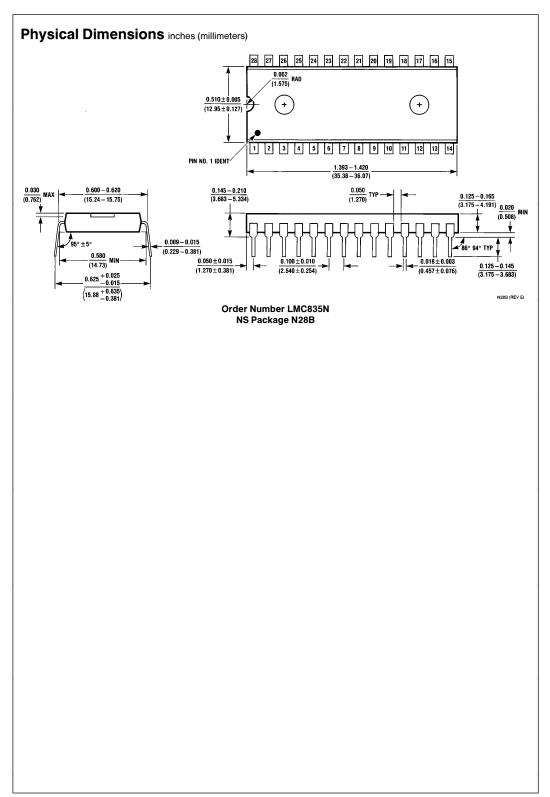
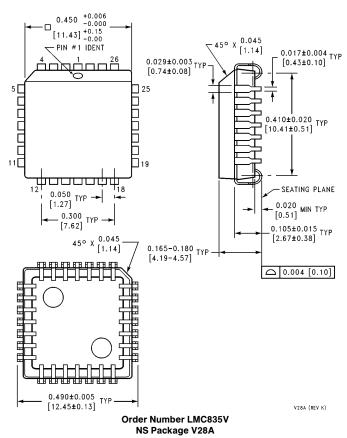


FIGURE 16. Reducing External Components





# Physical Dimensions inches (millimeters) (Continued)



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